N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

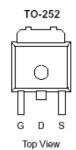
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
30	6 @ V _{GS} = 10V	75		
	8 @ V _{GS} = 4.5V	65		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C I _D 75			A		
Pulsed Drain Current ^b			300			
Continuous Source Current (Diode Conduction) a	I _S	30	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	50	W		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

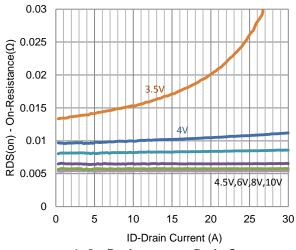
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$				V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	u/\	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			6	mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 18 \text{ A}$			8	11152	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		20		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.84		V	
Dynamic							
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		20			
Gate-Source Charge	Q_gs	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		7.3		nC	
Gate-Drain Charge	Q_gd	1D = 20 A		11			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_1 = 0.8 \Omega,$		10			
Rise Time	t _r	$I_{DS} = 13 \text{ V}, \text{ NL} = 0.0 \Omega_{2},$ $I_{D} = 20 \text{ A},$		13		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		51		ns	
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		21			
Input Capacitance	C _{iss}			1785			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		323		pF	
Reverse Transfer Capacitance	C_{rss}			285			

Notes

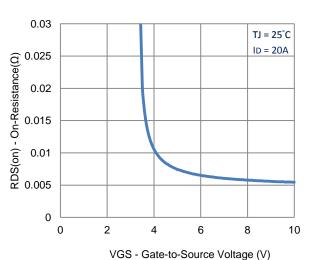
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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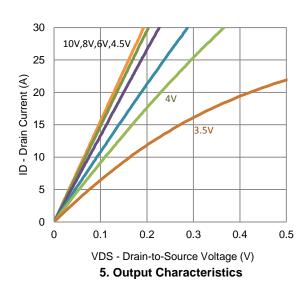
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current

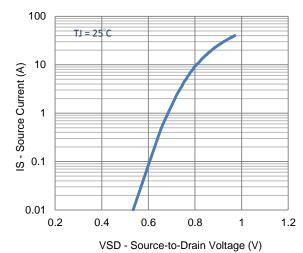


3. On-Resistance vs. Gate-to-Source Voltage

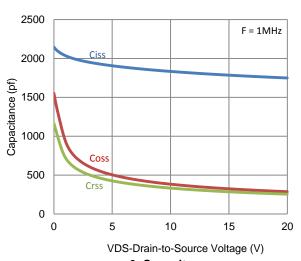


30 TJ = 25°C 25 ID - Drain Current (A) 20 15 10 5 0 0 1 2 3 5 6 VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

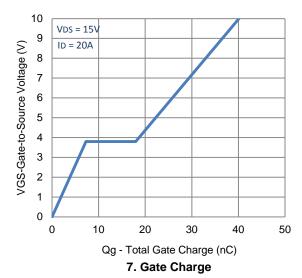


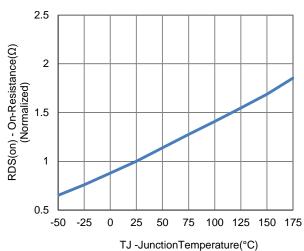
4. Drain-to-Source Forward Voltage

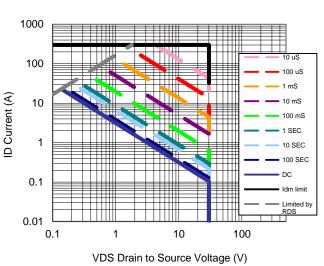


6. Capacitance

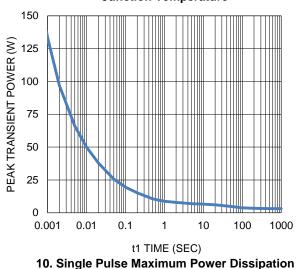
Typical Electrical Characteristics



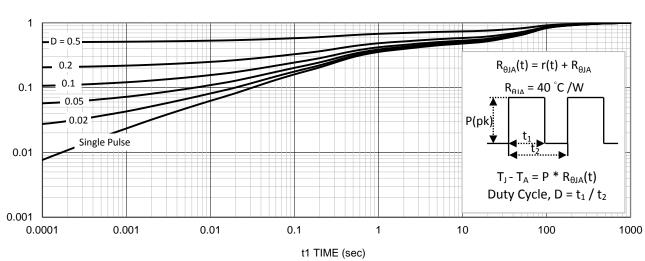






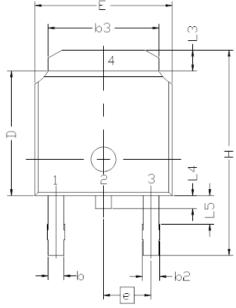


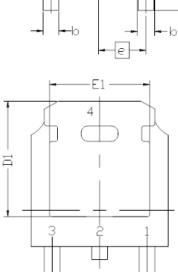
9. Safe Operating Area 1



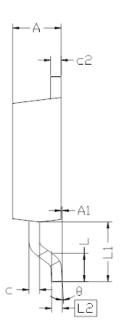
11. Normalized Thermal Transient Junction to Ambient

Package Information





SINGLE ROWNEW



SYMBOL	DIMENS: MIN	IDNAL F Nom	REQMTS MAX
E	6.40	6,60	6.731
L	1.40	1.52	1.77
L1	2	.743 RI	F
L2	0.	.508 BS	
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е		286 BS	
Α	2,20	2.30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5,30		
E1	4.40		
Θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.